

2SD684A

SILICON NPN TRIPLE DIFFUSED TYPE
(DARLINGTON POWER)

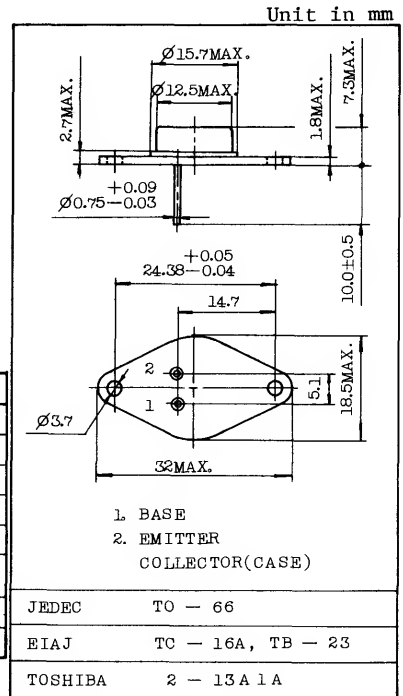
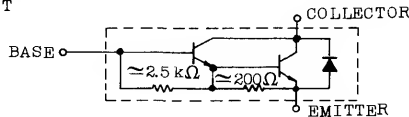
IGNITER APPLICATIONS.
HIGH VOLTAGE SWITCHING APPLICATIONS.
FEATURES:

- High DC Current Gain
: $h_{FE}=600$ (Min.) ($V_{CE}=2V$, $I_C=2A$)
- Monolithic Construction With Built-In Base-Emitter Shunt Resistor.

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	600	V
Collector-Emitter Voltage	V_{CE0}	400	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	6	A
Base Current	I_B	1	A
Collector Power Dissipation ($T_c=25^\circ C$)	PC	30	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-65~150	$^\circ C$

EQUIVALENT CIRCUIT



Mounting kit No.AC74
Weight : 5.9g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CB0}	$V_{CB}=600V$, $I_E=0$	-	-	0.5	mA
Emitter Cut-off Current	I_{EB0}	$V_{EB}=5V$, $I_C=0$	-	-	3	mA
Collector-Emitter Breakdown Voltage	$V(BR)_{CEO}$	$I_C=10mA$, $I_B=0$	400	-	-	V
DC Current Gain	$h_{FE}(1)$	$V_{CE}=2V$, $I_C=2A$	600	-	-	
	$h_{FE}(2)$	$V_{CE}=2V$, $I_C=4A$	100	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4A$, $I_B=0.04A$	-	-	2.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=4A$, $I_B=0.04A$	-	-	2.5	V
Emitter-Collector Forward Voltage	V_{ECF}	$I_E=4A$, $I_B=0$	-	-	3.0	V
Collector Output Capacitance	C_{ob}	$V_{CB}=50V$, $I_E=0$, $f=1MHz$	-	35	-	pF
Switching Time	Turn-on Time	t_{on}	-	1	-	
	Storage Time	t_{stg}	-	8	-	μs
	Fall Time	t_f	$I_{B1} = -I_{B2} = 0.04A$ DUTY CYCLE $\leq 1\%$ $V_{CC}=100V$	-	5	-

STATIC CHARACTERISTICS

